

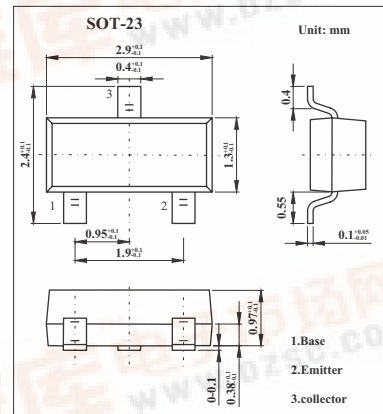
SMD Type Transistors

Switching Transistors

FMMT4126

■ Features

- Switching transistors.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Rating | Unit |
|---|-----------------------------------|-------------|------|
| Collector-base voltage | V _{CBO} | -25 | V |
| Collector-emitter voltage | V _{CEO} | -25 | V |
| Emitter-base voltage | V _{EBO} | -4 | V |
| Collector current | I _c | -200 | mA |
| Power dissipation | P _{tot} | 330 | mW |
| Operating and storage temperature range | T _j , T _{stg} | -55 to +150 | °C |

FMMT4126

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|--|----------------------|---|-----|-----|-------|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C =-10mA, | -25 | | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | I _C =-1mA, | -25 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =-10mA, | -4 | | | V |
| Collector cutoff current | I _{CBO} | V _{CE} =-20V | | | -50 | nA |
| Emitter cut-off current | I _{EBO} | V _{EB} =-3V | | | -50 | nA |
| Collector-emitter saturation voltage * | V _{CE(sat)} | I _C =-50mA, I _B =-5mA | | | -0.4 | V |
| Base-emitter saturation voltage * | V _{BE(sat)} | I _C =-50mA, I _B =-5mA | | | -0.95 | V |
| DC current gain * | h _{FE} | I _C =-2mA, V _{CE} =-1V | 120 | | 360 | |
| Current-gain-bandwidth product | f _T | I _C =-10mA, V _{CE} =-20V f=100MHz | 250 | | | MHz |
| Output capacitance | C _{obo} | V _{CB} =-5V, I _E =0, f=140KHz | | | 4.5 | pF |
| Input capacitance | C _{ibo} | V _{BE} =-0.5V, I _C =0, f=140KHz | | | 10 | pF |
| Noise figure | NF | V _{CE} =-5V I _C =-200mA, R _g =-2K? f=30Hz to 15KHz at -3dB points | | | 4 | dB |
| Small signal current transfer | h _{fe} | I _C =-2mA, V _{CE} =-1V, f=1KHz | 120 | 180 | | |
| Delay time | t _d | V _{CC} =-3V, I _C =-10mA, I _{B1} =-1mA | | | 25 | ns |
| Rise time | t _r | V _{BE(off)} =-0.5V | | | 18 | ns |
| Storage time | t _s | V _{CC} =-3V, I _C =-10mA | | | 140 | ns |
| Fall time | t _f | I _{B1} = I _{B2} =-1mA | | | 15 | ns |

* Pulse test: t_p ≤ 300 μs; d ≤ 0.02.

■ Marking

| | |
|---------|----|
| Marking | ZE |
|---------|----|